



20V/9A N-Channel Junction Power MOSFET

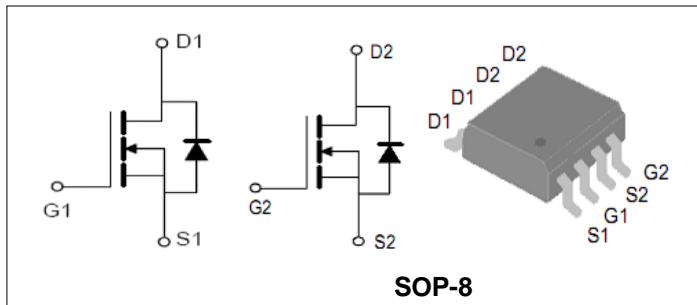
Features

- Low On-Resistance
- Fast Switching

BVDSS	20	V
ID	9	A
RDS(on)@VGS=10V	7	mΩ
RDS(on)@VGS=4.5V	8	mΩ
RDS(on)@VGS=2.5V	10	mΩ

Applications

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)



SOP-8

Order Information

Product	Package	Marking	Reel Size	Reel	Carton
PTS9926B	SOP-8	PTS9926B	13inch	3000PCS	48000PCS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{(BR)DSS}	Drain-Source Breakdown Voltage	20	V	
V _{GS}	Gate-Source Voltage	±12	V	
T _J	Maximum Junction Temperature	150	°C	
T _{STG}	Storage Temperature Range	-55 to 150	°C	
I _S	Diode Continuous Forward Current	TA =25°C	8	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested (Sillicon Limit) (Note1)	TA =25°C	30	A
I _D	Continuous Drain current	TA =25°C	9	A
P _D	Maximum Power Dissipation	TA =25°C	2.5	W
R _{θJC}	Thermal Resistance Junction-to-Case (Note2)		50	°C/W

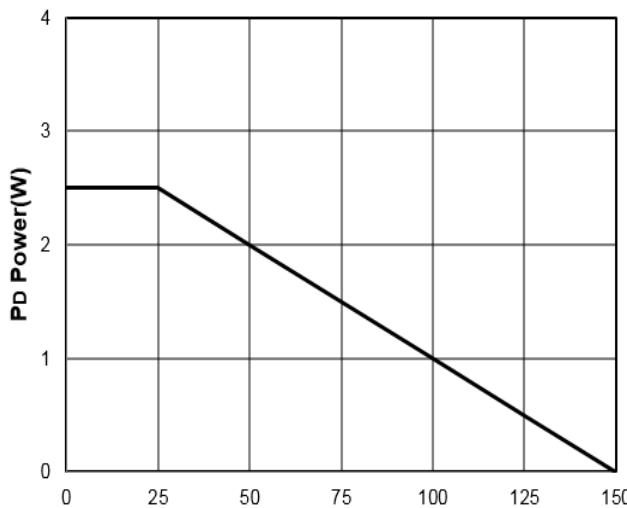
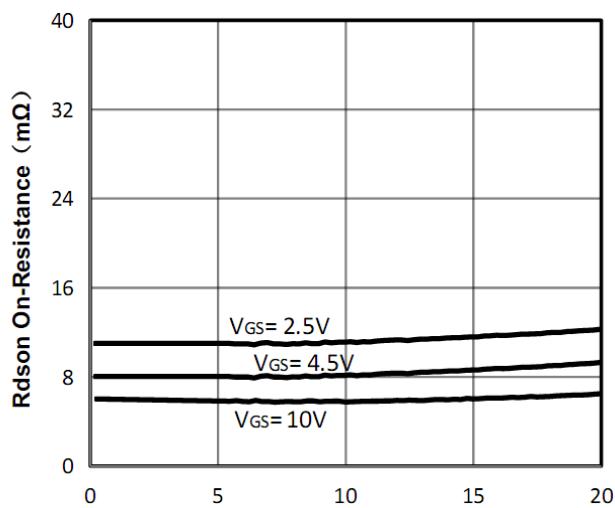
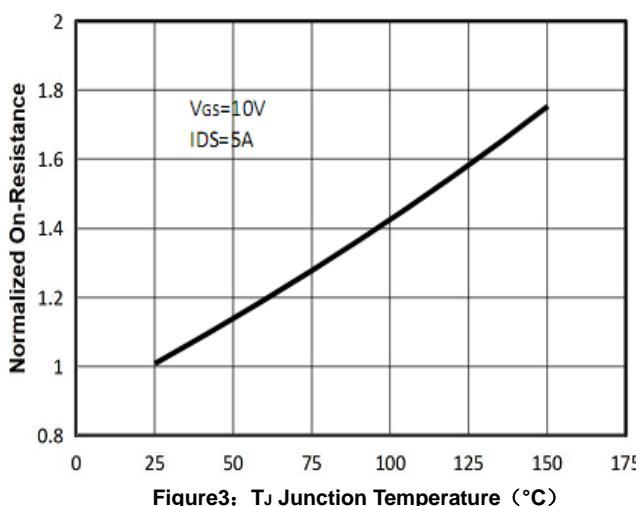
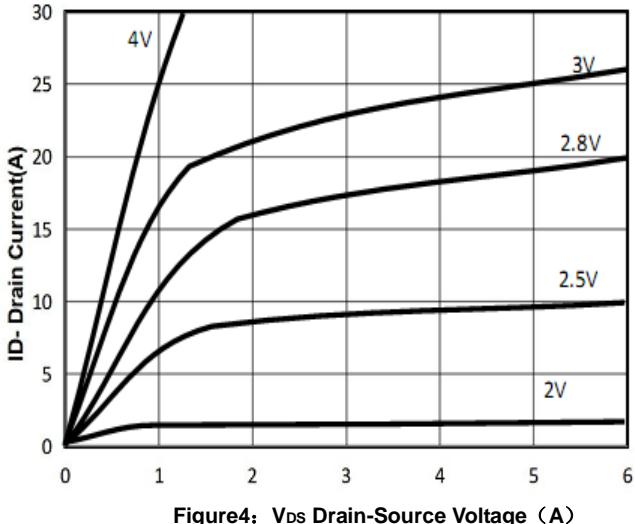
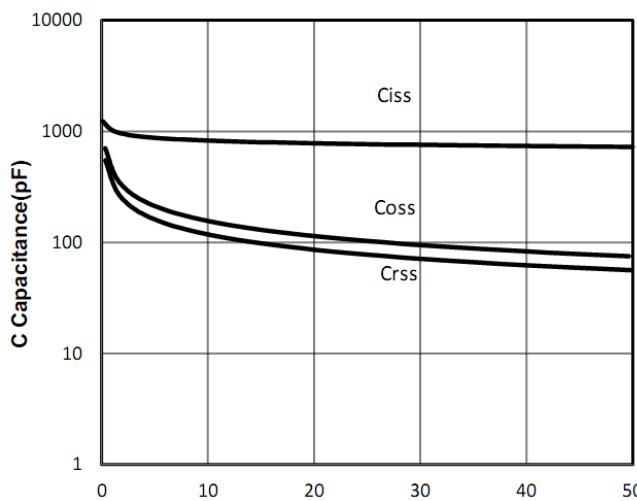
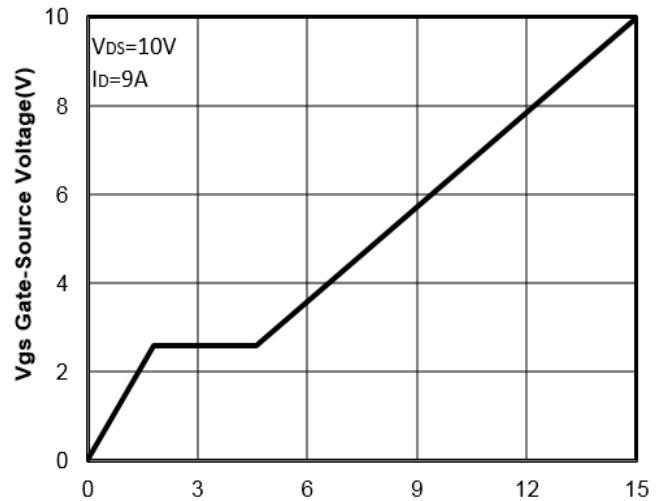


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Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain- Source Breakdown Voltage	$VGS=0V$ $ID=250\mu A$	20	--	--	V
I_{DSS}	Zero Gate Voltage Drain current	$VDS=20V, VGS=0V$	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	$VGS=\pm 10V, VDS=0V$	--	--	± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$VDS=VGS, ID=250\mu A$	0.5	--	1.2	V
$R_{DS(ON)}$	Drain-Source On-State Resistance (Note3)	$VGS=10V, ID=9A$	--	7	11	mΩ
		$VGS=4.5V, ID=8A$	--	8	16	
		$VGS=2.5V, ID=6A$	--	10	18	
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated) (Note4)						
C_{iss}	Input Capacitance	$VDS=10V,$ $VGS=0V,$ $F=1MHz$	--	900	--	pF
C_{oss}	Output Capacitance		--	162	--	pF
C_{rss}	Reverse Transfer Capacitance		--	105	--	pF
Q_g	Total Gate Charge	$VDS=10V,$ $ID=9A,$ $VGS=10V$	--	15	--	nC
Q_{gs}	Gate-Source Charge		--	1.8	--	nC
Q_{gd}	Gate-Drain Charge		--	2.8	--	nC
Switching Characteristics (Note4)						
$t_{d(on)}$	Turn-on Delay Time	$VDS=15V,$ $R_L=0.5\Omega,$ $RG=3\Omega,$ $VGS=10V$	--	4.5	--	nS
t_r	Turn-on Rise Time		--	9.2	--	nS
$t_{d(off)}$	Turn-off Delay Time		--	18.7	--	nS
t_f	Turn-off Fall Time		--	3.3	--	nS
Source- Drain Diode Characteristics@ TJ = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	$ISD=8A, VGS=0V$	--	--	1.2	V

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: pulse width ≤ 300 us, duty cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

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Typical Characteristics

Figure1: TJ Junction Temperature (°C)

Figure2: Id Drain Current (A)

Figure3: TJ Junction Temperature (°C)

Figure4: VDS Drain-Source Voltage (A)

Figure5: VDS Drain-Source Voltage (V)

Figure6: Qg Gate Charge (nC)

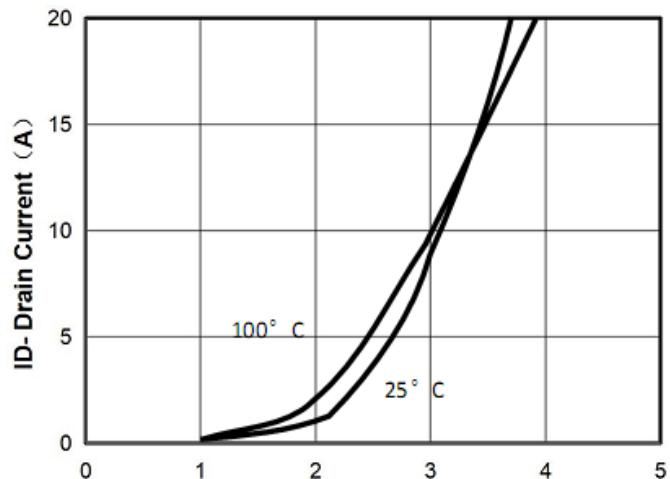
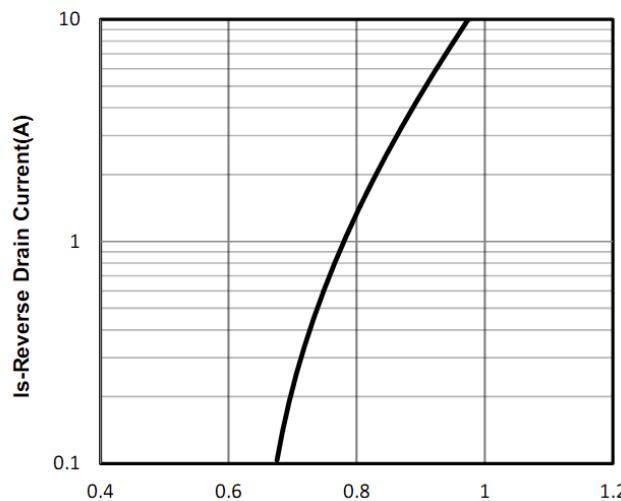
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Figure 7: V_{sd} Source-Drain Voltage (V)

Figure 8: V_{gs} Gate-Source Voltage (V)

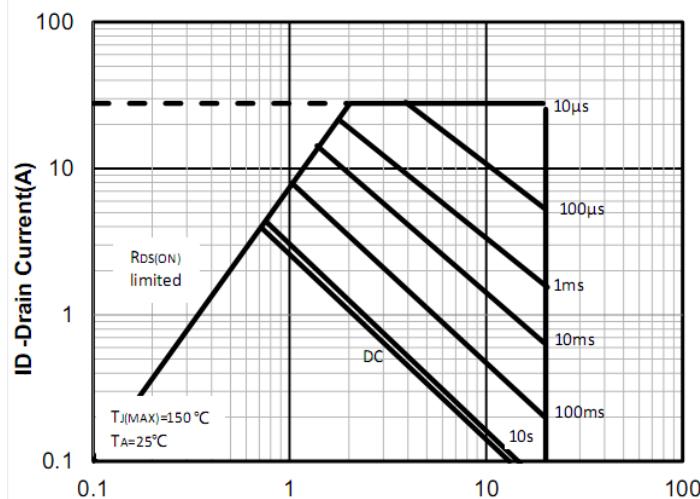


Figure 9: V_{ds} Drain -Source Voltage (V)

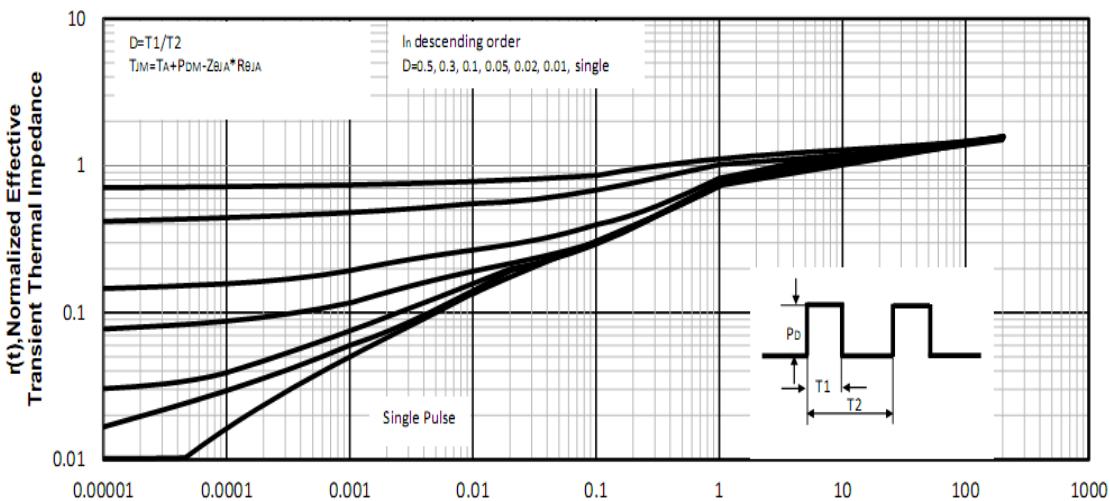
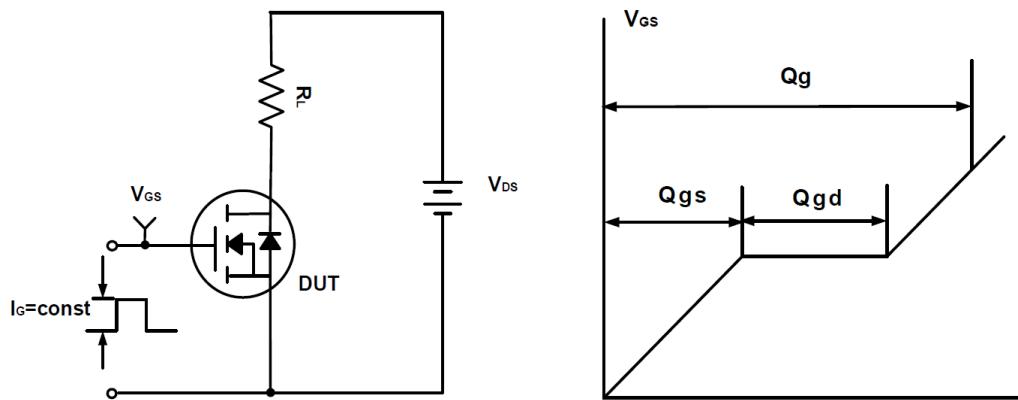
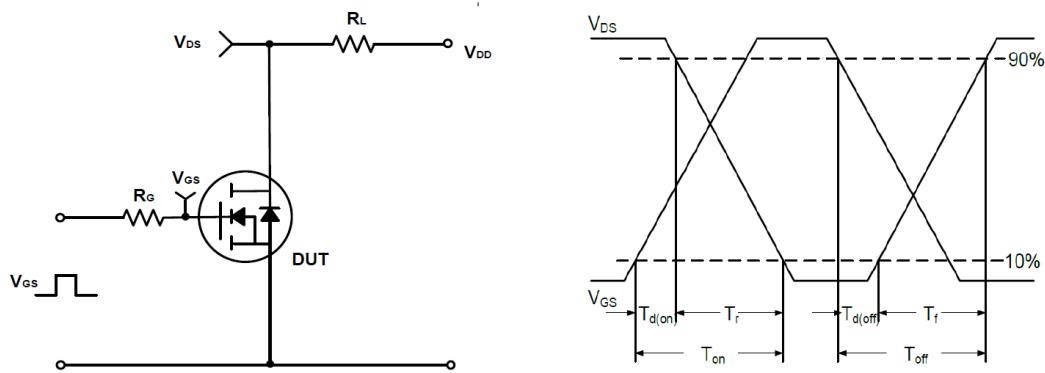
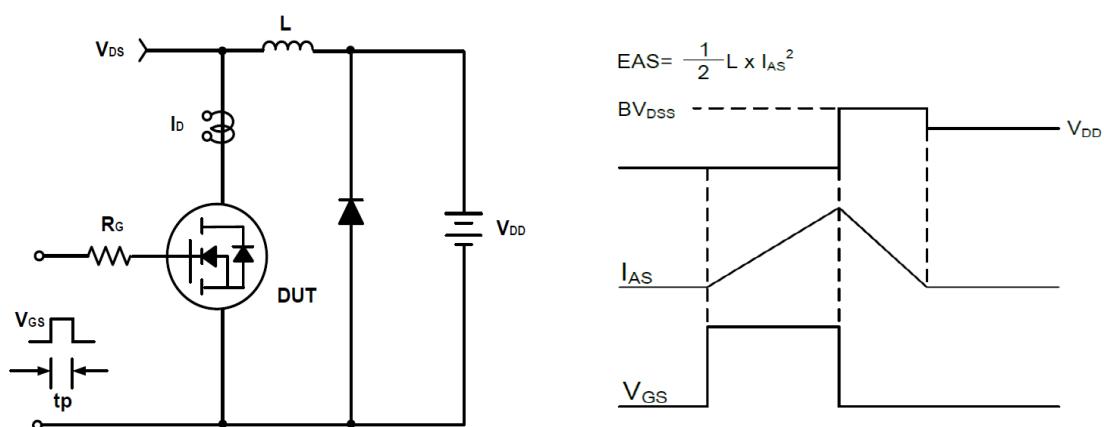
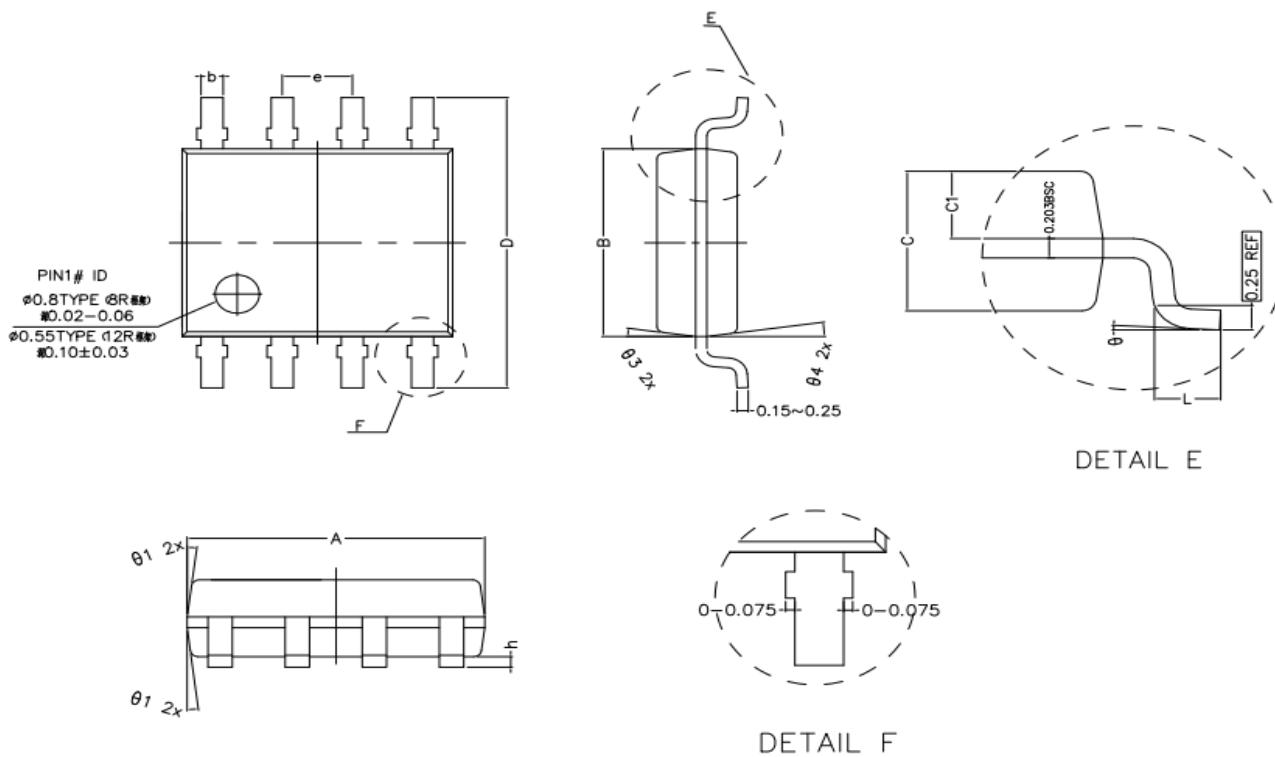


Figure 10: Square Wave Pulse Duration (sec)

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Test Circuit and Waveform:

Figure A Gate Charge Test Circuit & Waveforms

Figure B Switching Test Circuit & Waveforms

Figure C Unclamped Inductive Switching Circuit & Waveforms

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SOP-8 Package Outline Dimensions (Units: mm)


COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	4.800	4.900	5.000
B	3.800	3.900	4.000
C	1.350	1.450	1.550
C1	0.650	0.700	0.750
D	5.900	6.100	6.300
L	0.500	0.600	0.700
b	0.350	0.400	0.450
h	0.050	0.150	0.250
e	1.270 TYPE		
θ_1	7° TYPE(8R)	12° TYPE(12R)	
θ_2	7° TYPE(8R)	10° TYPE(12R)	
θ_3	8° TYPE(8R)	12° TYPE(12R)	
θ_4	8° TYPE(8R)	10° TYPE(12R)	
θ	0° ~ 8°		